NSN 5961-00-211-1979

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-211-1979 **Inclosure Material:** Metal **Overall Length:** 1.592 inches **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.552 inches and 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 25.0 repetitive peak reverse voltage, peak total value and 0.9 gate trigger voltage, instantaneous **Current Rating Per Characteristic:** 35.00 amperes collector current, dc megahertz **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0